

claims) are authorized to be charged in two originally-executed copies of an Amendment Transmittal Letter filed herewith.

IN THE CLAIMS:

Please add the following new claims:

Sub 113
30. (New) A method for forming a CVD-TiN film, wherein a titanium nitride (TiN) film is formed on a dielectric film that includes an oxide material formed by a CVD film forming process within a CVD film forming device, said method comprising:

heating a substrate provided with said dielectric film in said CVD film forming device, within an atmosphere with a non-reactive gas with respect to said dielectric film including said oxide material; and

forming said titanium nitride (TiN) film on said dielectric film in said CVD film forming device.

31. (New) A method for forming a CVD-TiN film according to claim 30, wherein said dielectric film including said oxide material is a tantalum oxide (Ta₂O₅) film.

32. (New) A method for forming a CVD-TiN film according to claim 31, wherein said substrate is heated to a temperature of approximately 400°C to no greater than approximately 700°C.